

Dual Schmitt-Trigger Inverter

NL27WZ14

The NL27WZ14 is a high performance dual inverter with Schmitt-Trigger inputs operating from a 1.65 to 5.5 V supply.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 3.2 ns t_{PD} at $V_{CC} = 5$ V (Typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Sink 32 mA at 4.5 V
- Available in SC-88, SC-74, TSOP-6 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant


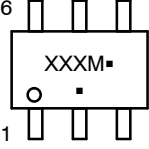

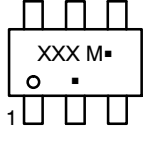

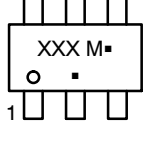






Figure 1. Logic Symbol



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MARKING DIAGRAMS		
	SC-88 DF SUFFIX CASE 419B-02	
	SC-74 CASE 318F-05	
	TSOP-6 CASE 318G-02	
	UDFN6 1.45x1.0, 0.5P CASE 517AQ	
	UDFN6 1x1, 0.35P CASE 517BX	

X, XXX = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

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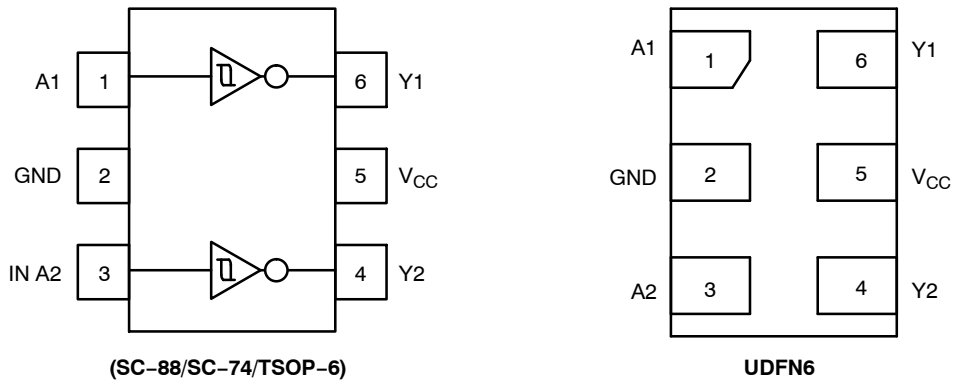


Figure 2. Pinout (Top View)

PIN ASSIGNMENT

Pin	Function
1	A1
2	GND
3	A2
4	Y2
5	V _{CC}
6	Y1

FUNCTION TABLE

A Input	Y Output
L	H
H	L

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MAXIMUM RATINGS

Symbol	Characteristics	Value	Units
V _{CC}	DC Supply Voltage TSOP-6, SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V _{IN}	DC Input Voltage TSOP-6, SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V _{OUT}	DC Output Voltage TSOP-6, SC-88 (NLV) Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} +0.5 -0.5 to +7.0 -0.5 to +7.0	V
	DC Output Voltage SC-88, SC-74, UDFN6 Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} +0.5 -0.5 to +6.5 -0.5 to +6.5	V
I _{IK}	DC Input Diode Current, V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current, V _{OUT} < GND	-50	mA
I _{OUT}	DC Output Source/Sink Current	±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pin	±100	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 secs	260	°C
T _J	Junction Temperature under Bias	+150	°C
θ _{JA}	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6 377 320 154	°C/W
P _D	Power Dissipation in Still Air	SC-88 SC-74 UDFN6 332 390 812	mW
MSL	Moisture Sensitivity	Level 1	-
F _R	Flameability Rating Oxygen Index: 28 to 34	UL 94-V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3) Human Body Model Charged Device Model (NLV) Charged Device Model	2000 1000 N/A	V
I _{LATCHUP}	Latchup Performance (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	1.65	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
V _{OUT}	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	0	V _{CC}	V
		0	5.5	
		0	5.5	
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Transition Rise or Fall Rate V _{CC} = 1.65 V to 1.95 V V _{CC} = 2.3 V to 2.7 V V _{CC} = 3.0 V to 3.6 V V _{CC} = 4.5 V to 5.5 V	0	No Limit	ns
		0	No Limit	
		0	No Limit	
		0	No Limit	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{T+}	Positive Input Threshold Voltage		1.65	-	1.0	1.4	-	1.4	-	1.4	V
			2.3	-	1.5	1.8	-	1.8	-	1.8	
			2.7	-	1.7	2	-	2	-	2	
			3	-	1.9	2.2	-	2.2	-	2.2	
			4.5	-	2.7	3.1	-	3.1	-	3.1	
			5.5	-	3.3	3.6	-	3.6	-	3.6	
V _{T-}	Negative Input Threshold Voltage		1.65	0.2	0.5	-	0.2	-	0.2	-	V
			2.3	0.4	0.75	-	0.4	-	0.4	-	
			2.7	0.5	0.87	-	0.5	-	0.5	-	
			3	0.6	1.0	-	0.6	-	0.6	-	
			4.5	1.0	1.5	-	1.0	-	1.0	-	
			5.5	1.2	1.9	-	1.2	-	1.2	-	
V _H	Input Hysteresis Voltage		1.65	0.1	0.48	0.9	0.1	0.9	0.1	0.9	V
			2.3	0.25	0.75	1.1	0.25	1.1	0.25	1.1	
			2.7	0.3	0.83	1.15	0.3	1.15	0.3	1.15	
			3	0.4	0.93	1.2	0.4	1.2	0.4	1.2	
			4.5	0.6	1.2	1.5	0.6	1.5	0.6	1.5	
			5.5	0.7	1.4	1.7	0.7	1.7	0.7	1.7	
V _{OH}	High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.65 to 5.5	V _{CC} - 0.1	V _{CC}	-	V _{CC} - 0.1	-	V _{CC} - 0.1	-	V
		I _{OH} = -4 mA	1.65	1.29	1.52	-	1.29	-	1.29	-	
		I _{OH} = -8 mA	2.3	1.9	2.1	-	1.9	-	1.9	-	
		I _{OH} = -12 mA	2.7	2.2	2.4	-	2.2	-	2.2	-	
		I _{OH} = -16 mA	3	2.4	2.7	-	2.4	-	2.4	-	
		I _{OH} = -24 mA	3	2.3	2.5	-	2.3	-	2.3	-	
		I _{OH} = -32 mA	4.5	3.8	4	-	3.8	-	3.8	-	
V _{OL}	Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.65 to 5.5	-	-	0.1	-	0.1	-	0.1	V
		I _{OL} = 4 mA	1.65	-	0.08	0.24	-	0.24	-	0.24	
		I _{OL} = 8 mA	2.3	-	0.2	0.3	-	0.3	-	0.3	
		I _{OL} = 12 mA	2.7	-	0.22	0.4	-	0.4	-	0.4	
		I _{OL} = 16 mA	3	-	0.28	0.4	-	0.4	-	0.4	
		I _{OL} = 24 mA	3	-	0.38	0.55	-	0.55	-	0.55	
		I _{OL} = 32 mA	4.5	-	0.42	0.55	-	0.55	-	0.55	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1	-	10	-	10	μA
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5	-	-	1	-	10	-	10	μA

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AC ELECTRICAL CHARACTERISTICS

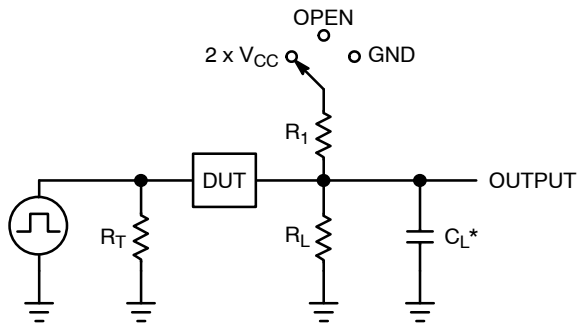
Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation Delay, A to Y (Figures 3 and 4)	R _L = 1 MΩ, C _L = 15 pF	1.65 to 1.95	-	7.1	13	-	14.5	-	15.5	ns
			2.3 to 2.7	-	4.3	7.4	-	8.1	-	9.1	
		R _L = 1 MΩ, C _L = 15 pF	3.0 to 3.6	-	3.3	5	-	5.5	-	6.5	
			4.5 to 5.5	-	2.7	4.1	-	4.5	-	5.5	
			R _L = 500 Ω, C _L = 50 pF	3.0 to 3.6	-	4	6	-	6.6	-	
		4.5 to 5.5		-	3.2	4.9	-	5.4	-	6.4	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	2.5	pF
C _{OUT}	Output Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4.0	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V _{CC} = 3.3 V, V _{IN} = 0 V or V _{CC} 10 MHz, V _{CC} = 5.0 V, V _{IN} = 0 V or V _{CC}	11 12.5	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} \cdot I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} \cdot I_{CC} \cdot V_{CC}$.

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C_L includes probe and jig capacitance
 R_T is Z_{OUT} of pulse generator (typically 50 Ω)
 $f = 1$ MHz

Figure 3. Test Circuit

Test	Switch Position	C_L , pF	R_L , Ω	R_1 , Ω
t_{PLH} / t_{PHL}	Open	See AC Characteristics Table		
t_{PLZ} / t_{PZL}	$2 \times V_{CC}$	-	-	-
		See AC Characteristics Table		
t_{PHZ} / t_{PZH}	GND	-	-	-
		See AC Characteristics Table		

X = Don't Care

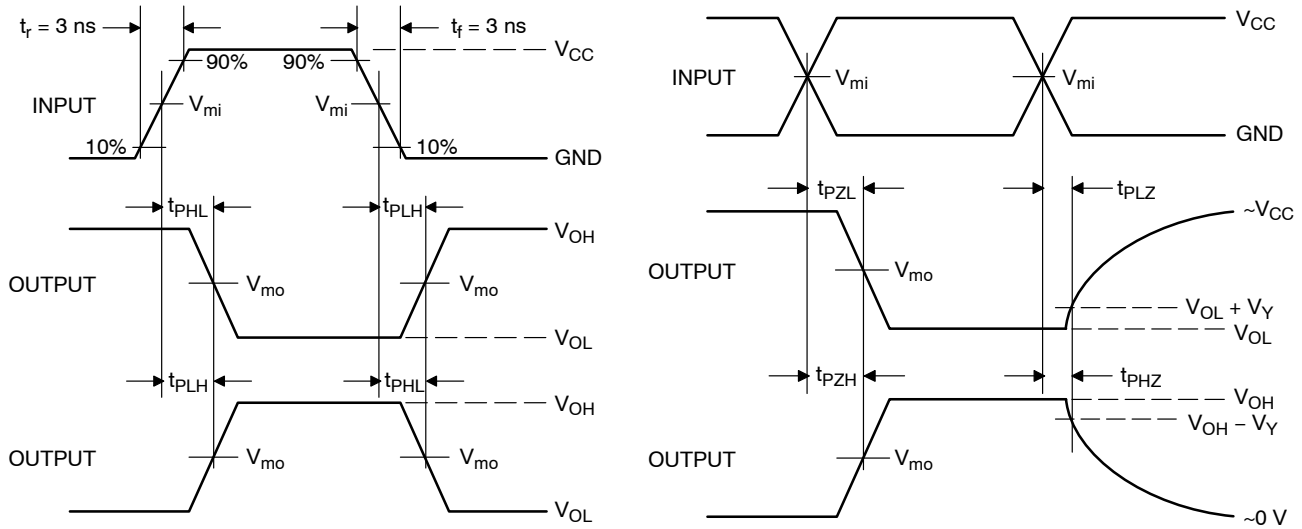


Figure 4. Switching Waveforms

V_{CC} , V	V_{mi} , V	V_{mo} , V		V_Y , V
		t_{PLH} , t_{PHL}	t_{PZL} , t_{PLZ} , t_{PZH} , t_{PHZ}	
1.65 to 1.95	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.15
2.3 to 2.7	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.15
3.0 to 3.6	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.3
4.5 to 5.5	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.3

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ORDERING INFORMATION

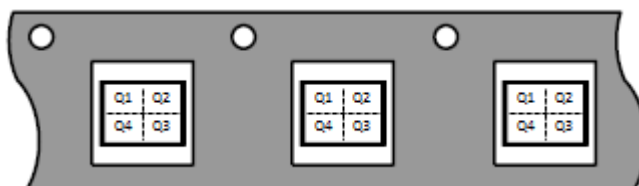
Device	Package	Specific Device Code	Pin1 Orientation (See below)	Shipping [†]
NL27WZ14DFT2G	SC-88	MA	Q4	3000 / Tape & Reel
NL27WZ14DFT4G	SC-88	MA	Q4	10000 / Tape & Reel
NLV27WZ14DFT2G*	SC-88	MA	Q4	3000 / Tape & Reel
NL27WZ14DTT1G	TSOP-6	MA	Q4	3000 / Tape & Reel
NL27WZ14DBVT1G	SC-74	MA	Q4	3000 / Tape & Reel
NL27WZ14MU1TCG	UDFN6, 1.45 x 1.0, 0.5P	P (Rotated 90° CW)	Q4	3000 / Tape & Reel
NL27WZ14MU3TCG	UDFN6, 1.0 x 1.0, 0.35P	3 (Rotated 90° CW)	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

Pin 1 Orientation in Tape and Reel

Direction of Feed



MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

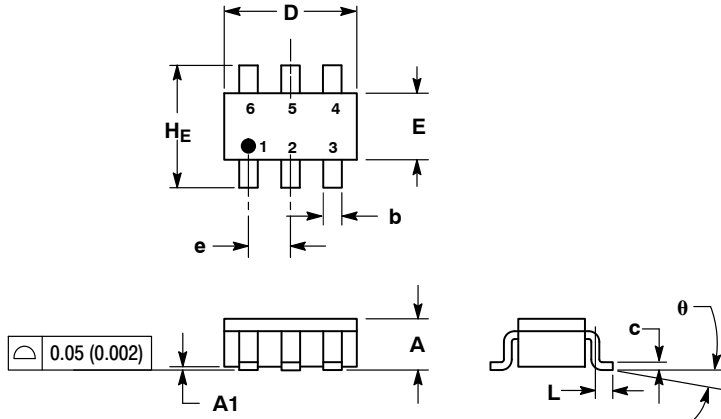
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SC-74 CASE 318F-05 ISSUE N

DATE 08 JUN 2012

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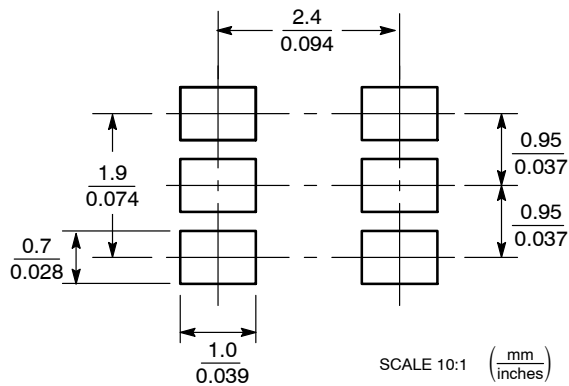


NOTES:

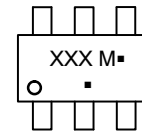
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

SOLDERING FOOTPRINT*



GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- | | | | | | |
|---|--|---|--|---|---|
| <p>STYLE 1:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE</p> | <p>STYLE 2:
PIN 1. NO CONNECTION
2. COLLECTOR
3. EMITTER
4. NO CONNECTION
5. COLLECTOR
6. BASE</p> | <p>STYLE 3:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1</p> | <p>STYLE 4:
PIN 1. COLLECTOR 2
2. EMITTER 1/EMITTER 2
3. COLLECTOR 1
4. EMITTER 3
5. BASE 1/BASE 2/COLLECTOR 3
6. BASE 3</p> | <p>STYLE 5:
PIN 1. CHANNEL 1
2. ANODE
3. CHANNEL 2
4. CHANNEL 3
5. CATHODE
6. CHANNEL 4</p> | <p>STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE</p> |
| <p>STYLE 7:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1</p> | <p>STYLE 8:
PIN 1. EMITTER 1
2. BASE 2
3. COLLECTOR 2
4. EMITTER 2
5. BASE 1
6. COLLECTOR 1</p> | <p>STYLE 9:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2</p> | <p>STYLE 10:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE</p> | <p>STYLE 11:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR</p> | |

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DESCRIPTION:	SC-74	PAGE 1 OF 1

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

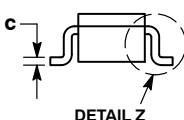
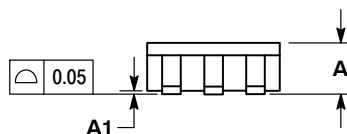
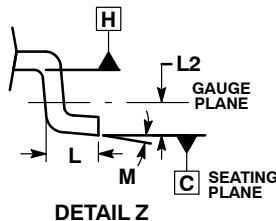
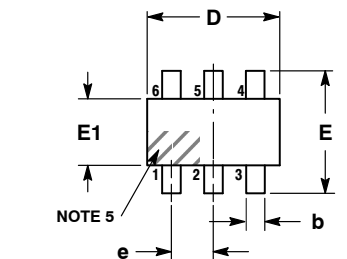
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SCALE 2:1

TSOP-6 CASE 318G-02 ISSUE V

DATE 12 JUN 2012

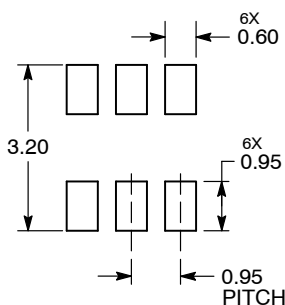


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
 5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	-	10°

- | | | | | | |
|--|--|---|---|---|--|
| <p>STYLE 1:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN</p> | <p>STYLE 2:
PIN 1. EMITTER 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. BASE 2
6. COLLECTOR 2</p> | <p>STYLE 3:
PIN 1. ENABLE
2. N/C
3. R BOOST
4. Vz
5. V in
6. V out</p> | <p>STYLE 4:
PIN 1. N/C
2. V in
3. NOT USED
4. GROUND
5. ENABLE
6. LOAD</p> | <p>STYLE 5:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2</p> | <p>STYLE 6:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR</p> |
| <p>STYLE 7:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. N/C
5. COLLECTOR
6. EMITTER</p> | <p>STYLE 8:
PIN 1. Vbus
2. D(in)
3. D(in)+
4. D(out)+
5. D(out)
6. GND</p> | <p>STYLE 9:
PIN 1. LOW VOLTAGE GATE
2. DRAIN
3. SOURCE
4. DRAIN
5. DRAIN
6. HIGH VOLTAGE GATE</p> | <p>STYLE 10:
PIN 1. D(OUT)+
2. GND
3. D(OUT)-
4. D(IN)-
5. VBUS
6. D(IN)+</p> | <p>STYLE 11:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1/GATE 2</p> | <p>STYLE 12:
PIN 1. I/O
2. GROUND
3. I/O
4. I/O
5. VCC
6. I/O</p> |
| <p>STYLE 13:
PIN 1. GATE 1
2. SOURCE 2
3. GATE 2
4. DRAIN 2
5. SOURCE 1
6. DRAIN 1</p> | <p>STYLE 14:
PIN 1. ANODE
2. SOURCE
3. GATE
4. CATHODE/DRAIN
5. CATHODE/DRAIN
6. CATHODE/DRAIN</p> | <p>STYLE 15:
PIN 1. ANODE
2. SOURCE
3. GATE
4. DRAIN
5. N/C
6. CATHODE</p> | <p>STYLE 16:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE</p> | <p>STYLE 17:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR</p> | |

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



- | | |
|--|---|
| <p>XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package</p> | <p>XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package</p> |
|--|---|

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

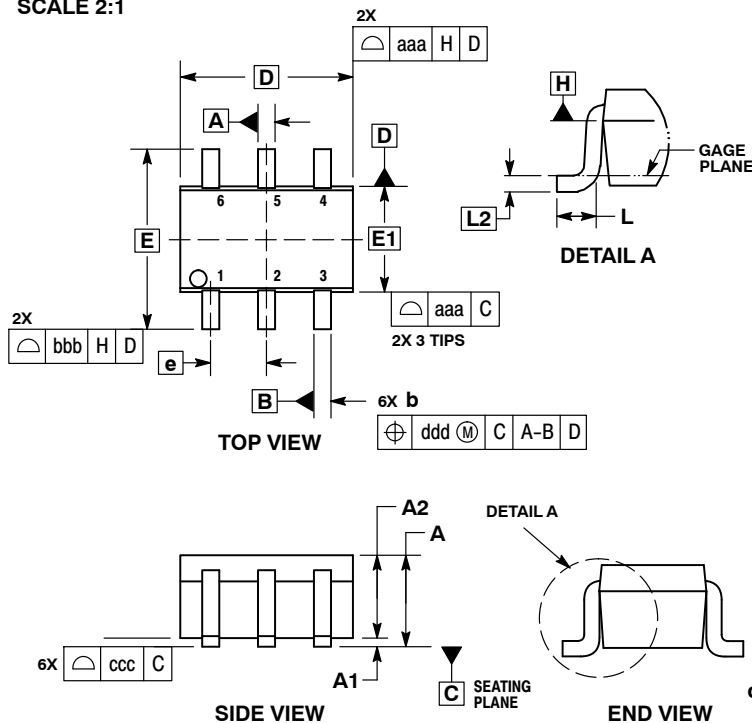
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1
SCALE 2:1

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y

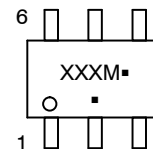
DATE 11 DEC 2012



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

GENERIC MARKING DIAGRAM*



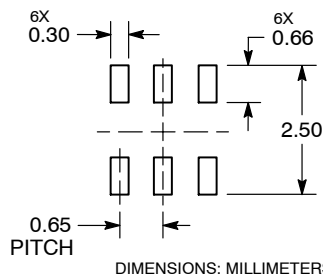
XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y

DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

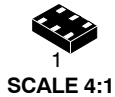
Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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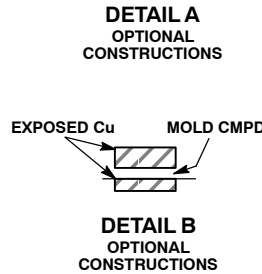
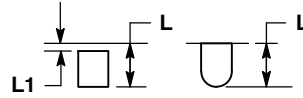
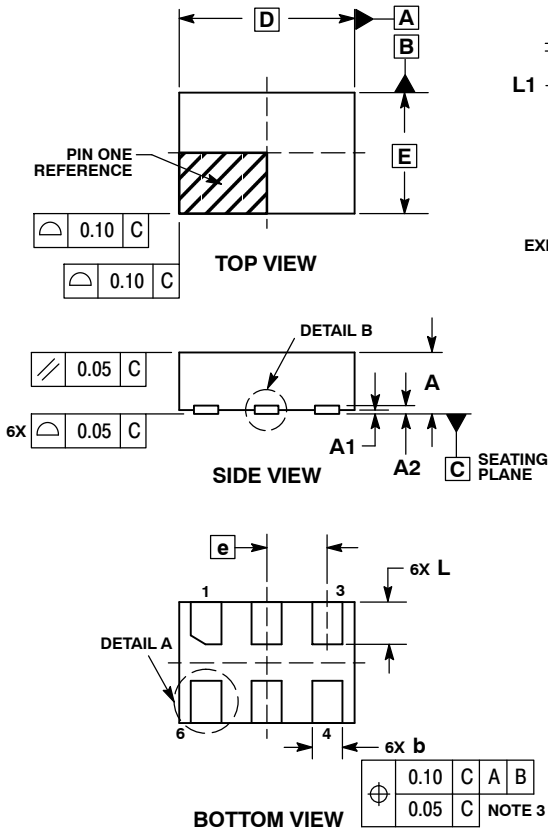
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



UDFN6, 1.45x1.0, 0.5P
CASE 517AQ-01
ISSUE O

DATE 15 MAY 2008



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A2	0.07	REF
b	0.20	0.30
D	1.45	BSC
E	1.00	BSC
e	0.50	BSC
L	0.30	0.40
L1	---	0.15

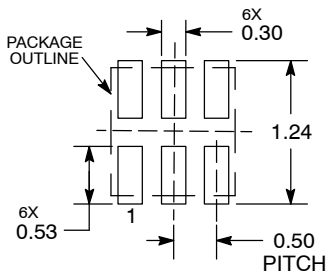
GENERIC MARKING DIAGRAM*



- X = Specific Device Code
- M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.

MOUNTING FOOTPRINT



DIMENSIONS: MILLIMETERS

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